



IR390DM..CCB SERIES

STANDARD RECOVERY DIODES

■ Junction Size:	Rectangular 390 X 270 mils
■ Wafer Size:	4"
■ V_{RRM} Class:	800 to 1200 V
■ Passivation Process:	Glassivated MOAT
■ Reference IR Packaged Part:	85EPS Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{FM} Maximum Forward Voltage	1.15 V	$T_J = 25^\circ\text{C}$, $I_F = 85\text{ A}$
V_{RRM} Reverse Breakdown Voltage Range	800 to 1200 V	$T_J = 25^\circ\text{C}$, $I_{RRM} = 100\text{ }\mu\text{A}$ (1)

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 μm)
Chip Dimensions	390x270 mils (9.91x6.86mm) - seedrawing
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	300 μm , $\pm 10\text{ }\mu\text{m}$
Maximum Width of Sawing Line	45 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	Seedrawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

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Bulletin I0103J 10/01

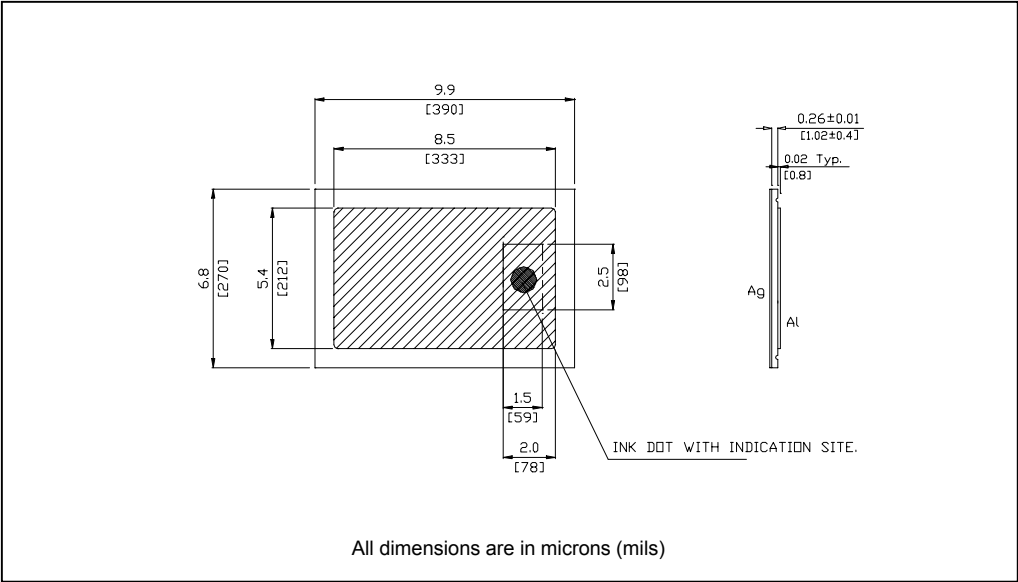


Ordering Information Table

Device Code						
IR	390	D	M	12	C	CB
1	2	3	4	5	6	7
1	- International Rectifier Device					
2	- Chip Dimension in Mils					
3	- Type of Device: D = Wire Bondable Standard Recovery Diode					
4	- Passivation Process: M = Glassivated MOAT					
5	- Voltage code: Code x 100 = V_{RRM}					
6	- Metallization: C = Aluminium (Anode) - Silver (Cathode)					
7	- CB = Probed Uncut Die (wafer in box) None = Probed Die in chip carrier					

Available Class
08 = 800 V
10 = 1000V
12 = 1200 V

Outline Table



Wafer Layout

